	Substitute for form 1449/PTO				Application Number	10/788,857	
0	INE				Filing Date:	February 26, 2004	
	19	Information	Disclosure	•	First Named Inventor:	Chao I. WU	
_ FEB	B 0 7 2006 Statement By Applicant			t	Art Unit:	2824	
PATER	/ببع	(Use as many sheets as necessary)			Examiner Name:	N. Nguyen	
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Non Patent Literature Documents

Examiner Initial	Cite No.	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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	W	

Examiner Signature	Date Considered	

Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.